

PUBLICATIONS

A. Publications in International Journals and Reviews

- A.1** "Photoluminescence properties of porous silicon/fluorene dye composites ", Fakis, M., Zacharatos, F., Gianneta, V., Persephonis, P., Giannetas, V., Nassiopoulou, A.G., Materials Science and Engineering B, . Article in Press. 2009
- A.2** "Photoluminescence in the blue spectral region from fluorene molecules embedded in porous anodic alumina thin films on silicon", M. Fakis, V. Gianneta, P. Persephonis, V. Giannetas, A. G. Nassiopoulou, Optical Materials, Optical Materials, 31 (8), pp. 1184-1188, 2009
- A.3** "Effect of exciton migration on the light emission properties in silicon nanocrystal ensembles", Gardelis, S., Nassiopoulou, A.G., Vouroutzis, N., Frangis, N., Journal of Applied Physics, 105 (11), art. no. 113509, 2009 (Selected for the July 2009, Issue (vol. 8, issue 7) of Virtual Journal of Ultrafast Science, 2009)
- A.4** "Formation of porous anodic alumina templates in selected micrometer-sized areas on a Si substrate. Application for growing ordered Ti nanopillars", Gianneta, V., Huffman, M., Nassiopoulou, A.G., Physica Status Solidi (A) Applications and Materials, 206 (6), pp. 1309-1312, 2009
- A.5** "Highly ordered hexagonally arranged sub-200 nm diameter vertical cylindrical pores on p-type Si using non-lithographic pre-patterning of the Si substrate", Zacharatos, F., Gianneta, V., Nassiopoulou, A.G., Physica Status Solidi (A) Applications and Materials, 206 (6), pp. 1286-1289, 2009
- A.6** "Enhancement and red shift of photoluminescence (PL) of fresh porous Si under prolonged laser irradiation or ageing: Role of surface vibration modes", Gardelis, S., Nassiopoulou, A.G., Mahdouani, M., Bourguiga, R., Jaziri, S., Physica E: Low-Dimensional Systems and Nanostructures, 41 (6), pp. 986-989, 2009
- A.7** "Laterally ordered 2-D arrays of Si and Ge nanocrystals within SiO₂ thin layers for application in non-volatile memories", Nassiopoulou, A.G., Olzierski, A., Tsoi, E., Salonidou, A., Kokonou, M., Stoica, T., Vescan, L., International Journal of Nanotechnology, 6 (1-2), pp. 18-34 (2009)
- A.8** "RF characterization and isolation properties of mesoporous Si by on-chip coplanar waveguide measurements", H. Contopanagos, F. Zacharatos, A. G. Nassiopoulou, Solid-State Electronics, 52 (11), pp. 1730-1734 (2008)
- A.9** "Morphology, structure, chemical composition, and light emitting properties of very thin anodic silicon films fabricated using short single pulses of current", S. Gardelis, A. G. Nassiopoulou, F. Petraki, S. Kennou, I. Tsiaoussis, N. Frangis, Journal of Applied Physics, 103 (10), art. no. 103536 (2008)

- A.10** “Highly ordered hexagonally arranged nanostructures on silicon through a self-assembled silicon-integrated porous anodic alumina masking layer”, F. Zacharatos, V. Gianneta and A. G. Nassiopoulou, *Nanotechnology* 19, 495306 (2008)
- A.11** “Self-assembled hexagonal ordering of Si nanocrystals embedded in SiO₂ nanodots”, A. G. Nassiopoulou, V. Gianneta, M. Huffman, M. A. Reading, J. A. Van Den Berg, I. Tsiaoussis, N. Frangis, *Nanotechnology* 19, 495605 (2008)
- A.12** “Columnar growth of ultra-thin nanocrystalline Si films on quartz by Low Pressure Chemical Vapor Deposition: Accurate control of vertical size”, Lioutas, Ch.B., Vouroutzis, N., Tsiaoussis, I., Frangis, N., Gardelis, S., Nassiopoulou, A.G., *Physica Status Solidi (A) Applications and Materials*, 205 (11), pp. 2615-2620 (2008)
- A.13** “Growth and electrical characterization of thin conductive Au nanoparticle chains on oxidized Si substrates between electrodes for sensor applications”, A. Zoy, A. G. Nassiopoulou, *Phys. Status Solidi (A) Applications and Materials*, 205 (11), pp. 2621-2624 (2008)
- A.14** “Broadband electrical characterization of macroporous silicon at microwave frequencies”, H. Contopanagos, D. N. Pagonis, A. G. Nassiopoulou, *Physica Status Solidi (A) Applications and Materials*, 205 (11), pp. 2548-2551 (2008)
- A.15** “A thermal vacuum sensor fabricated on plastic substrate - Study in various operation modes”, A. Petropoulos, G. Kaltsas, A. G. Nassiopoulou, *Physica Status Solidi (A) Applications and Materials*, 205 (11), pp. 2639-2642 (2008)
- A.16** “Auger recombination in silicon nanocrystals embedded in SiO₂ wide band-gap lattice”, M. Mahdouani, R. Bourguiga, S. Jaziri, S. Gardelis, A. G. Nassiopoulou, *Physica Status Solidi (A) Applications and Materials*, 205 (11), pp. 2630-2634 (2008)
- A.17** “Copper-filled macroporous Si and cavity underneath for microchannel heat sink technology”, F. Zacharatos, A. G. Nassiopoulou, *Physica Status Solidi (A) Applications and Materials*, 205 (11), pp. 2513-2517 (2008)
- A.18** “Enhancement and red shift of photoluminescence (PL) of fresh porous Si under prolonged laser irradiation or ageing: Role of surface vibration modes“, S. Gardelis, A. G. Nassiopoulou, M. Mahdouani, R. Bourguiga, S. Jaziri, *Physica E: Low-Dimensional Systems and Nanostructures*, doi:10.1016/j.physe.2008.08.021(2008)
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- A.22** “Ultrafast time-resolved spectroscopy of Si nanocrystals embedded in SiO₂ matrix”, E. Lioudakis, A. Emporas, A. Othonos, A. G. Nassiopoulou, *Journal of Alloys and Compounds*, doi:10.1016/j.jallcom.2008.07.193, Article in Press (2008)

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- A.31** "A silicon thermal accelerometer without solid proof mass using porous silicon thermal isolation" D. Goustouridis, G. Kaltsas and A. G. Nassiopoulou IEEE Sensors Journal, vol. 7 No 7 983 (2007)
- A.32** "Quantum confinement and interface structure of Si nanocrystals of sizes 3-5 nm embedded in α -SiO₂" E. Lioudakis, A. Othonos, G. C. Hadjisavvas, P. C. Kelires and A. G. Nassiopoulou" Physica E 38 128-134 (2007)
- A.33** "Integrated inductors on porous silicon", H. Contopanagos, A. G. Nassiopoulou, Physica Status Solidi (A) 204 (5), pp. 1454-1458 (2007)
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